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List of Publications by Year
in descending order

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24 papers	579 citations	840776 11 h-index	940533 16 g-index
24 all docs	24 docs citations	24 times ranked	642 citing authors

#	Article	IF	Citations
1	Singleâ€Shot Fabrication of Semiconductingâ€“Superconducting Nanowire Devices. Advanced Functional Materials, 2021, 31, 2102388.	14.9	12
2	Molybdenum nanopillar arrays: Fabrication and engineering. Physica E: Low-Dimensional Systems and Nanostructures, 2021, 134, 114903.	2.7	5
3	Tuning of Source Material for InAs/InGaAsSb/GaSb Application-Specific Vertical Nanowire Tunnel FETs. ACS Applied Electronic Materials, 2020, 2, 2882-2887.	4.3	11
4	Nanowire Tunnel FET with Simultaneously Reduced Subthermionic Subthreshold Swing and Off-Current due to Negative Capacitance and Voltage Pinning Effects. Nano Letters, 2020, 20, 3255-3262.	9.1	58
5	Trap-Aware Compact Modeling and Power-Performance Assessment of III-V Tunnel FET. , 2018, , .		0
6	An Experimental Study of Heterostructure Tunnel FET Nanowire Arrays: Digital and Analog Figures of Merit from 300K to 10K. , 2018, , .		10
7	Effect of Gate Oxide Defects on Tunnel Transistor RF Performance. , 2018, , .		0
8	Vertical Nanowire TFETs With Channel Diameter Down to 10 nm and Point S_{MIN} of 35 mV/Decade. IEEE Electron Device Letters, 2018, 39, 1089-1091.	3.9	35
9	Capacitance Measurements in Vertical IIIâ€“V Nanowire TFETs. IEEE Electron Device Letters, 2018, 39, 943-946.	3.9	5
10	Impact of source doping on the performance of vertical InAs/InGaAsSb/GaSb nanowire tunneling field-effect transistors. Nanotechnology, 2018, 29, 435201.	2.6	12
11	Impact of Non-idealities on the Performance of InAs/(In)GaAsSb/GaSb Tunnel FETs. Composants NanoÃ©lectroniques, 2018, 18, .	0.2	4
12	Individual Defects in InAs/InGaAsSb/GaSb Nanowire Tunnel Field-Effect Transistors Operating below 60 mV/decade. Nano Letters, 2017, 17, 4373-4380.	9.1	85
13	InAs/InGaAsSb/GaSb Nanowire Tunnel Field-Effect Transistors. IEEE Transactions on Electron Devices, 2017, 64, 4746-4751.	3.0	53
14	Low-Frequency Noise in IIIâ€“V Nanowire TFETs and MOSFETs. IEEE Electron Device Letters, 2017, 38, 1520-1523.	3.9	19
15	Impact of Band-Tails on the Subthreshold Swing of III-V Tunnel Field-Effect Transistor. IEEE Electron Device Letters, 2017, 38, 1661-1664.	3.9	23
16	Random telegraph signal noise in tunneling field-effect transistors with S below 60 mV/decade. , 2017, , .		2
17	The impact of hetero-junction and oxide-interface traps on the performance of InAs/Si and InAs/GaAsSb nanowire tunnel FETs. , 2017, , .		5
18	Projected performance of experimental InAs/GaAsSb/GaSb TFET as millimeter-wave detector. , 2017, , .		0

#	Article	IF	Citations
19	Vertical InAs/GaAsSb/GaSb tunneling field-effect transistor on Si with S = 48 mV/decade and I<inf>on</inf> = 10 Î¼A/Î¼m for I<inf>off</inf> = 1 nA/Î¼m at V<inf>ds</inf> = 0.3 V. , 2016, , .		45
20	Scaling of Vertical InAsâ€“GaSb Nanowire Tunneling Field-Effect Transistors on Si. IEEE Electron Device Letters, 2016, 37, 549-552.	3.9	56
21	III-V Heterostructure Nanowire Tunnel FETs. IEEE Journal of the Electron Devices Society, 2015, 3, 96-102.	2.1	53
22	Thin electron beam defined hydrogen silsesquioxane spacers for vertical nanowire transistors. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2014, 32, 051211.	1.2	8
23	High-Frequency Gate-All-Around Vertical InAs Nanowire MOSFETs on Si Substrates. IEEE Electron Device Letters, 2014, 35, 518-520.	3.9	77
24	RF characterization of vertical InAs nanowire MOSFETs with f<inf>t</inf> and f<inf>max</inf> above 140 GHz. , 2014, , .		1